ROITHNER LASERTECHNIK

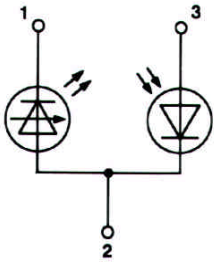
A-1040 WIEN, FLEISCHMANNGASSE 9
TEL: +43 -1- 586 52 43 FAX: +43 -1- 586 41 43
e-mail: rlt@mcb.at http://www.roithner.mcb.at

S6510MG TECHNICAL DATA

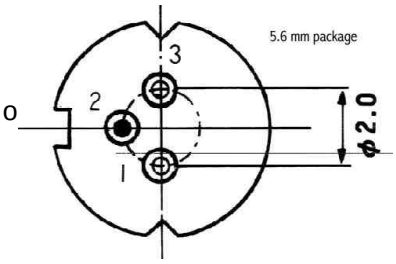
Visible Wavelength Laserdiode

Structure: **InGaAlP, index guided single transverse mode**
Lasing wavelength: **655nm typ.**
Output power: **10 mW, CW**
Package: **5.6 mm MG, TO-18**

PIN CONNECTION:



1) Laser diode cathode
2) Laser diode anode and photodiode catho
3) Photodiode anode



Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	10	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operation Case Temperature	T_C	-10 .. +60	°C
Storage Temperature	T_{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I_{th}			15	20	mA
Operation Current	I_{op}	P_o =10mW		26	40	mA
Operating Voltage	V_{op}	P_o =10mW		2.2	2.6	V
Lasing Wavelength	λ_p	P_o =10mW	650	655	660	nm
Beam Divergence	θ//	P_o =10mW	5	7	9	°
Beam Divergence	$\theta\perp$	P_o =10mW	30	32	38	°
Slope Efficiency	η		0.5	0.7	1	mW/mA
Monitor Current	I_m	P_o=10mW	50	200	500	µA